

FEATURES AND BENEFITS

- Differential current sensing cancels common mode fields, simplifying PCB layout
- Two user-settable faults for fast short-circuit protection and slower overcurrent detection
- Industry-leading noise performance with greatly improved bandwidth through proprietary amplifier and filter design techniques
- Patented integrated digital temperature compensation circuitry allows high accuracy over temperature in an open loop sensor
- 1.0 m Ω primary conductor resistance for low power loss and high inrush current-withstanding capability
- Small footprint, low-profile SOIC16 package suitable for space-constrained applications
- Integrated shield virtually eliminates capacitive coupling from current conductor to die due to high dV/dt voltage transients
- 5 V single supply operation with 0-3 V output swing
- Output voltage proportional to AC or DC current
- Factory-trimmed sensitivity and quiescent output voltage for improved accuracy
- 3600 Vrms Dielectric Strength certified under UL60950-1
- · High PSRR for noisy environments

PACKAGE:

16-Pin SOICW (suffix LA)





DESCRIPTION

The ACS720 is a high accuracy Hall-effect-based current sensor IC with multiple programmable fault levels intended for industrial and consumer applications with a focus on motor control and power inverter stage applications.

One of the key benefits of the ACS720 is to provide high isolation with a reduced bill of materials made possible by the proprietary IC SOIC16W package. The ACS720 works off of a single 5 V supply while maintaining an output voltage swing from 0 to 3 V, with a stable zero current output of 1.5 V. This allows the ACS720 to operate off of a 5 V supply while having an output which is compatible with typical 3.3 V ADCs found on many MCUs. Furthermore, the ACS720's high PSRR rejects the noise often found on the supplies in the power section of the PCB or system, maintaining high accuracy in noisy environments.

The device has dual fault functions that are user configurable. Fast and slow fault output allow for short-circuit and overcurrent fault detection. A user-created resistor divider from the power supply of the ACS720 is used to set the fault level. The fault outputs are open drain, allowing the user to pull them up to a compatible voltage for the MCU. The open-drain outputs also allow for implementing a simple logical OR of multiple sensor fault outputs.

The ACS720 also integrates differential current sensing, which rejects external magnetic fields, greatly simplifying board layout in 3-phase motor applications.

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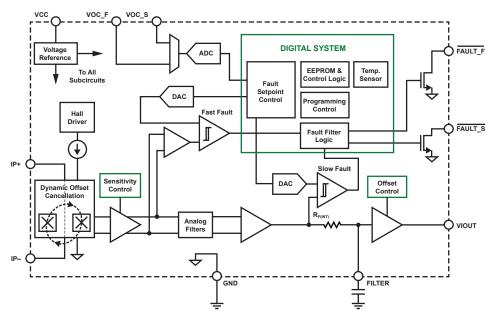


Figure 1: Functional Block Diagram

DESCRIPTION (continued)

Near closed-loop accuracy is achieved in this open-loop sensor due to Allegro's patented, digital temperature compensation, ultimately offering a smaller and more economical solution for many current sensing applications that traditionally rely on closed-loop core based sensors.

The ACS720 is provided in a small surface-mount SOIC16 package. The leadframe is plated with 100% matte tin, which is compatible with standard lead (Pb) free printed circuit board assembly processes. Internally, the device is Pb-free, except for flip-chip high-temperature Pb-based solder balls, currently exempt from RoHS. The device is fully calibrated prior to shipment from the factory.

SELECTION GUIDE

Part Number	Sensing Range, I _{PR} (A)	Sensitivity, Sens (Typ) (mV/A)	T _A (°C)	Packing*
ACS720KLATR-15AB-T	±15	90		
ACS720KLATR-35AB-T	±35	38.5	-40 to 125	Tape and Reel, 1000 pieces per reel
ACS720KLATR-65AB-T	±65	20.5		

^{*}Contact Allegro for packing options.

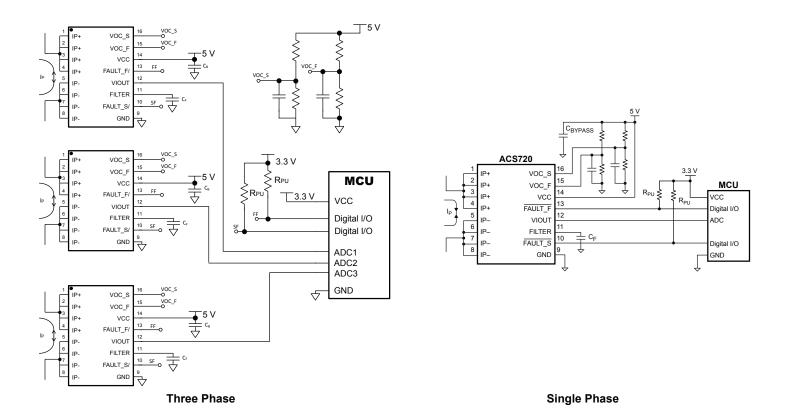


Figure 2: Typical Applications



High Accuracy, Dual Fault, Galvanically Isolated Current Sensor in SOIC16 Widebody Package

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Notes	Rating	Units
Supply Voltage	V _{CC}		6	V
Reverse Supply Voltage	V _{RCC}		-0.5	V
Filter Voltage	V _{FILTER}		25	V
Reverse Filter Voltage	V _{RFILTER}		-0.5	V
Output Voltages	V _{IOUT,} V _{FAULT_} S, V _{FAULT_} F		V _{CC} + 0.7	V
Reverse Output Voltage	V _{RIOUT,} V _{RFAULT_S,} V _{RFAULT_F}		-0.5	V
Input Pin Voltages	V _{OC_S,} V _{OC_F}		V _{CC} + 0.7	V
Reverse Input Pin Voltages	V _{ROC_S,} V _{ROC_F}		-0.5	V
Operating Ambient Temperature	T _A	Range K	-40 to 125	°C
Junction Temperature	T _{J(max)}		165	°C
Storage Temperature	T _{stg}		-65 to 170	°C

ISOLATION CHARACTERISTICS

Characteristic	Symbol	Notes	Value	Units
Dielectric Surge Strength Test Voltage	V _{SURGE}	Tested ±5 pulses at 2/minute in compliance to IEC 61000-4-5 1.2 µs (rise) / 50 µs (width).	10000	V
Dielectric Strength Test Voltage	V _{ISO}	Agency type-tested for 60 seconds per UL 60950-1 (edition 2). Production tested at 2250 V _{RMS} for 1 second in accordance with UL 60950-1.	3600	V _{RMS}
Marking Valtage for Desig Indiation		Maximum approved working voltage for basic (single)	870	V _{PK} or V _{DC}
Working Voltage for Basic Isolation	V _{WVBI}	isolation according to UL 60950-1 (edition 2).	616	V _{RMS}
Clearance	D _{cl}	Minimum distance through air from IP leads to signal leads.	7.5	mm
Creepage	D _{cr}	Minimum distance along package body from IP leads to signal leads.	7.5	mm

PINOUT DIAGRAM

_	
IP+ 1	16 VOC_S
IP+ 2	15 VOC_F
IP+ 3	14 VCC
IP+ 4	13 FAULT_F
IP- 5	12 VIOUT
IP- 6	11 FILTER
IP- 7	10 FAULT_S
IP-8	9 GND

TERMINAL LIST TABLE

Number	Name	Description
1 through 4	IP+	Terminals for current being sensed; fused internally
5 through 8	IP-	Terminals for current being sensed; fused internally
9	GND	Signal ground terminal
10	FAULT_S	Open drain slow fault output (low true)
11	FILTER	Add capacitor to set output filter pole location
12	VIOUT	Analog output signal
13	FAULT_F	Open drain fast fault output (low true)
14	VCC	Device power supply terminal
15	VOC_F	Sets the trip current level for the fast fault
16	VOC_S	Sets the trip current level for the slow fault



High Accuracy, Dual Fault, Galvanically Isolated Current Sensor in SOIC16 Widebody Package

COMMON OPERATING CHARACTERISTICS [1]: Over full range of T_A , and V_{CC} = 5 V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
ELECTRICAL CHARACTERISTIC	s					
Supply Voltage	V _{CC}		4.5	5.0	5.5	V
Supply Current	I _{CC}	V _{CC} = 5.0 V, output open	_	13	16	mA
Filter Resistance	R _{F(INT)}	T _A = 25°C	_	1.7	_	kΩ
Primary Conductor Resistance	R _{IP}	T _A = 25°C	_	1.0	_	mΩ
Power-On Time	t _{PO}	Time from when $V_{CC} > V_{CC(min)}$ to when the output reaches 90% of its steady-state level; $T_A = 25^{\circ}C$	_	70	-	μs
Fault Power-On Time [2]	t _{PO(FAULT)}	Time from when V _{CC} > V _{CC(min)} to when FAULT_S and FAULT_F will react to an overcurrent event	_	270	_	μs
OUTPUT SIGNAL CHARACTERIS	STICS					
Rise Time	t _R	T _A = 25°C, C _L = 1 nF, 1 V step on output	_	3	_	μs
Response Time	t _{RESPONSE}	T _A = 25°C, C _L = 1 nF, 1 V step on output	_	4	_	μs
Propagation Delay	t _{PD}	T _A = 25°C, C _L = 1 nF, 1 V step on output	_	1	_	μs
Internal Bandwidth	BW	Small signal –3 dB; C _L = 1 nF	_	120	_	kHz
Output Capacitance Load	C _L	VIOUT to GND	_	_	10	nF
Output Resistive Load	R _L	VIOUT to GND, VIOUT to VCC	10	_	_	kΩ
Output Source Current	I _{OUT(SRC)}	VIOUT shorted to GND	_	3	_	mA
Output Sink Current	I _{OUT(SNK)}	VIOUT shorted to VCC	_	30	_	mA
Saturation Voltage	V _{OL}	R_L = 10 kΩ (VIOUT to VCC)	_	_	150	mV
Clamp Voltage [4]	V _{CLAMP}		3.0	3.25	3.5	V
Noise Density	I _{ND}	Input-referenced noise density; $T_A = 25$ °C, $C_L = 4.7$ nF	-	220	_	μA /√(Hz)
Mailea		Input referenced noise at 120 kHz bandwidth; $T_A = 25$ °C; $C_L = 1$ nF; $C_F = 0$ nF	_	100	_	mA _{rms}
Noise	I _N	Input referenced noise at 20 kHz bandwidth; T _A = 25°C; C _L = 1 nF; C _F = 4.7 nF	-	31	-	mA _{rms}
Nonlinearity	E _{LIN}		_	±0.75	_	%
Dower Cumply Deinsting Deti-	DCDD	DC to 1 kHz	_	40	_	dB
Power Supply Rejection Ratio	PSRR	1 kHz to 20 kHz	_	30	_	dB

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High Accuracy, Dual Fault, Galvanically Isolated Current Sensor in SOIC16 Widebody Package

COMMON OPERATING CHARACTERISTICS [1] (continued): Over full range of T_A, and V_{CC} = 5 V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
FAULT CHARACTERISTICS						,
Fast Fault Response Time	t _{R(FF)}	Time from I _P rising above I _{FF} until $V_{FAULT_F} < V_{FAULTL}$ for a current step from 0 to 1.2 × I _{FAULT(FAST)} ; R _{PU} = 10 k Ω , 100 pF from FAULT_F to ground	_	1.5	2	μs
Slow Fault Response Time	t _{R(SF)}	Time from I _P rising above I _{SF} until $V_{FAULT_S} < V_{FAULTL}$ for a current step from 0 to 1.2 × I _{FAULT(SLOW)} ; R _{PU} = 10 k Ω , 100 pF from FAULT_S to ground	_	13	_	μs
Fast Fault Hysteresis [3]	I _{HYST(FF)}		_	0.06 × I _{PR}	_	Α
Slow Fault Hysteresis [3]	I _{HYST(SF)}		_	0.05 × I _{PR}	_	Α
Fault Output Low Voltage	V_{FAULTL}	R_{PU} = 10 $k\Omega,$ under fault condition, FAULT_S and FAULT_F pins	_	_	0.4	V
Fault Pull-Up Resistance	R _{PU}		4.7	_	500	kΩ
Fast Fault Range	I _{FAULT(F)}	Absolute value of I _P	1.0 × I _{PR}	_	2.25 × I _{PR}	Α
Slow Fault Range	I _{FAULT(S)}	Absolute value of I _P	0.5 × I _{PR}	_	1.25 × I _{PR}	Α
VOC input range	V _{VOC}	VOC_S, VOC_F	0.3 × V _{CC}	_	0.7 × V _{CC}	V
High Impedance Pin Input Current	I _{IN}	VOC_S, VOC_F	_	100	_	nA
VOC Sample Rate	f _{s(VOC)}	VOC_S, VOC_F	_	62.5	_	kHz
VOC Update Rate	f _{update(VOC)}	8 samples averaged per update	_	7.8	_	kHz

^[1] Device may be operated at higher primary current levels, I_P, ambient T_A, and internal leadframe temperature, provided that the Maximum Junction Temperature, $T_J(max)$, is not exceeded.



^[2] When $V_{CC} < V_{CC}$ (min), the faults remain in the no-fault state.

^[3] After the absolute value of I_P goes above I_{FAULT(F)} or I_{FAULT(S)}, tripping the internal fault comparator, I_P must go below I_{FAULT(F)} or I_{FAULT(S)} or I_{FAULT(S)} – I_{HYST(SF)}, before the internal fault comparator will reset.
[4] Clamp Voltage applies only to VIOUT pin.

High Accuracy, Dual Fault, Galvanically Isolated Current Sensor in SOIC16 Widebody Package

x15AB PERFORMANCE CHARACTERISTICS: Valid at $T_A = -40$ °C to 125°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Unit
NOMINAL PERFORMANCE				,		
Optimized Accuracy Range	I _{PR}		-15	_	15	Α
Sensitivity	Sens		_	90	_	mV/A
Zero-Current Output Voltage	V _{IOUT(Q)}	I _P = 0 A	_	1.5	_	V
Fast Fault Trip Level	I _{FF(HIGH)}	$VOC_F = 0.7 \times V_{CC}$	_	33.8	_	Α
	I _{FF(LOW)}	VOC_F = 0.54 × V _{CC}	_	26.3	_	Α
Clay Fault Trip Layel	I _{SF(HIGH)}	$VOC_S = 0.7 \times V_{CC}$	_	18.8	_	Α
Slow Fault Trip Level	I _{SF(LOW)}	$VOC_S = 0.3 \times V_{CC}$	_	7.5	-	А
TOTAL OUTPUT ERROR CO	MPONENTS	2 $E_{TOT}(I_P) = \{[V_{IOUT_ideal}(I_P) - V_{IOUT}(I_P)] / [Sens_{ideal}(I_P) \times I_P]\} \times 100$	(%)			
Total Output Error ^[3]	_	$I_{P} = I_{PR(max)}, T_{A} = 25^{\circ}C \text{ to } 125^{\circ}C$	-1.5	±0.8	1.5	%
	E _{TOT}	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4	±1.6	4	%
Sensitivity Error	E _{SENS}	$I_P = I_{PR(max)}, T_A = 25^{\circ}C \text{ to } 125^{\circ}C$	-1.5	±0.6	1.5	%
Sensitivity End		$I_P = I_{PR(max)}$, $T_A = -40$ °C to 25°C	-4	±1.6	4	%
Offset Voltage	V _{OE}	I _P = 0 A, T _A = 25°C to 125°C	-10	±4	10	mV
Oliset voltage	V OE	$I_P = 0 \text{ A}, T_A = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	-30	±9	30	mV
OVERCURRENT FAULT PER	FORMANCE					
		$VOC_F = 0.7 \times V_{CC}$, Positive I _P , T _A = 25°C	-10	±5	10	%
	E _{FF(HIGH)+}	$VOC_F = 0.7 \times V_{CC}$, Positive I _P , $T_A = 25$ °C to 125°C	-15	±5	15	%
		$VOC_F = 0.7 \times V_{CC}$, Positive I _P , $T_A = -40$ °C to 25°C	_	±25	_	%
		VOC_F = 0.7 × V _{CC} , Negative I _P , T _A = 25°C	-12	±6	12	%
	E _{FF(HIGH)}	VOC_F = $0.7 \times V_{CC}$, Negative I _P , T _A = 25° C to 125° C	-30	±20	30	%
Fast Fault Error		$VOC_F = 0.7 \times V_{CC}$, Negative I _P , $T_A = -40$ °C to 25°C	_	±35	_	%
T ast I ault LITOI		$VOC_F = 0.54 \times V_{CC}$, Positive I_P , $T_A = 25^{\circ}C$	-10	±7	10	%
	E _{FF(LOW)+}	$VOC_F = 0.54 \times V_{CC}$, Positive I_P , $T_A = 25^{\circ}C$ to $125^{\circ}C$	-15	±10	15	%
		$VOC_F = 0.54 \times V_{CC}$, Positive I_P , $T_A = -40$ °C to 25°C	_	±25	-	%
		VOC_F = $0.54 \times V_{CC}$, Negative I _P , T _A = 25° C	-15	±7	15	%
	E _{FF(LOW)-}	VOC_F = 0.54 × V _{CC} , Negative I _P , T _A = 25°C to 125°C	-40	±25	40	%
		VOC_F = 0.54 × V_{CC} , Negative I_P , $T_A = -40$ °C to 25°C	_	±45	_	%
Slow Fault Error	E _{SF(HIGH)}	$VOC_S = 0.7 \times V_{CC}$, I_P rising	-6	±3	6	%
Slow I dult LITUI	E _{SF(LOW)}	$VOC_S = 0.3 \times V_{CC}$, I_P rising	-12	±5	12	%

^[1] Typical values with +/- are 3 sigma values.



^[2] A single part will not have both the maximum/minimum sensitivity error and maximum/minimum offset voltage, as that would violate the maximum/minimum total output error specification. Also, 3 sigma distribution values are combined by taking the square root of the sum of the squares. [3] Percentage of I_P , with $I_P = I_{PR(max)}$.

High Accuracy, Dual Fault, Galvanically Isolated Current Sensor in SOIC16 Widebody Package

x35AB PERFORMANCE CHARACTERISTICS: Valid at $T_A = -40^{\circ}$ C to 125°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Unit
NOMINAL PERFORMANCE						
Optimized Accuracy Range	I _{PR}		-35	_	35	А
Sensitivity	Sens		_	38.5	_	mV/A
Zero-Current Output Voltage	V _{IOUT(Q)}	I _P = 0 A	_	1.5	_	V
Fast Fault Trip Level	I _{FF(HIGH)}	$VOC_F = 0.7 \times V_{CC}$	_	78.8	-	Α
	I _{FF(LOW)}	$VOC_F = 0.38 \times V_{CC}$	_	43.8	-	Α
Clay Fault Trip Layol	I _{SF(HIGH)}	$VOC_S = 0.7 \times V_{CC}$	_	43.8	-	Α
Slow Fault Trip Level	I _{SF(LOW)}	$VOC_S = 0.3 \times V_{CC}$	_	17.5	-	Α
TOTAL OUTPUT ERROR CO	MPONENTS !	^{2]} $E_{TOT}(I_P) = \{[V_{IOUT_ideal}(I_P) - V_{IOUT}(I_P)] / [Sens_{ideal}(I_P) \times I_P]\} \times 100$	(%)			
Total Output Error ^[3]	_	$I_{P} = I_{PR(max)}, T_{A} = 25^{\circ}C \text{ to } 125^{\circ}C$	-1.5	±0.6	1.5	%
	E _{TOT}	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4	±1.5	4	%
Sensitivity Error	E _{SENS}	$I_P = I_{PR(max)}, T_A = 25^{\circ}C \text{ to } 125^{\circ}C$	-1.5	±0.6	1.5	%
Sensitivity Error		$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4	±1.5	4	%
Offset Voltage	V _{OE}	I _P = 0 A, T _A = 25°C to 125°C	-10	±3.5	10	mV
	V OE	$I_P = 0 \text{ A}, T_A = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	-30	±9	30	mV
OVERCURRENT FAULT PER	FORMANCE					
		$VOC_F = 0.7 \times V_{CC}$, Positive I _P , $T_A = 25$ °C	-10	±5	10	%
	E _{FF(HIGH)+}	VOC_F = 0.7 × V_{CC} , Positive I_{P} , T_{A} = 25°C to 125°C	-10	±5	10	%
		VOC_F = 0.7 × V_{CC} , Positive I_P , $T_A = -40$ °C to 25°C	_	±15	_	%
		VOC_F = 0.7 × V _{CC} , Negative I _P , T _A = 25°C	-10	±5	10	%
	E _{FF(HIGH)}	VOC_F = 0.7 × V _{CC} , Negative I _P , T _A = 25°C to 125°C	-15	±10	15	%
Fast Fault Error		VOC_F = 0.7 × V_{CC} , Negative I_P , $T_A = -40$ °C to 25°C	_	±20	_	%
Fast Fault Elloi		$VOC_F = 0.38 \times V_{CC}$, Positive I_P , $T_A = 25$ °C	-20	±12	20	%
	E _{FF(LOW)+}	$VOC_F = 0.38 \times V_{CC}$, Positive I_P , $T_A = 25$ °C to 125°C	-20	±12	20	%
		$VOC_F = 0.38 \times V_{CC}$, Positive I _P , $T_A = -40^{\circ}C$ to 25°C	_	±25	_	%
		VOC_F = 0.38 × V _{CC} , Negative I _P , T _A = 25°C	-20	±12	20	%
	E _{FF(LOW)} -	VOC_F = 0.38 × V _{CC} , Negative I _P , T _A = 25°C to 125°C	-30	±18	30	%
		VOC_F = 0.38 × V _{CC} , Negative I _P , T _A = -40°C to 25°C	_	±32	_	%
Clay Fault Fran	E _{SF(HIGH)}	$VOC_S = 0.7 \times V_{CC}$, I_P rising	-6	±3	6	%
Slow Fault Error	E _{SF(LOW)}	$VOC_S = 0.3 \times V_{CC}$, I _P rising	-10	±5	10	%

^[1] Typical values with +/- are 3 sigma values.



^[2] A single part will not have both the maximum/minimum sensitivity error and maximum/minimum offset voltage, as that would violate the maximum/minimum total output error specification. Also, 3 sigma distribution values are combined by taking the square root of the sum of the squares.

^[3] Percentage of I_P , with $I_P = I_{PR(max)}$

High Accuracy, Dual Fault, Galvanically Isolated Current Sensor in SOIC16 Widebody Package

x65AB PERFORMANCE CHARACTERISTICS: Valid at $T_A = -40$ °C to 125°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Unit
NOMINAL PERFORMANCE						
Optimized Accuracy Range	I _{PR}		-65	_	65	А
Sensitivity	Sens		_	20.5	_	mV/A
Zero-Current Output Voltage	V _{IOUT(Q)}	I _P = 0 A	_	1.5	_	V
Fast Fault Trip Level	I _{FF(HIGH)}	$VOC_F = 0.7 \times V_{CC}$	_	146.3	-	Α
	I _{FF(LOW)}	$VOC_F = 0.38 \times V_{CC}$	_	81.3	_	Α
Slow Fault Trip Level	I _{SF(HIGH)}	$VOC_S = 0.7 \times V_{CC}$	_	81.3	-	Α
Slow Fault Trip Level	I _{SF(LOW)}	$VOC_S = 0.3 \times V_{CC}$	_	32.5	-	Α
TOTAL OUTPUT ERROR CO	MPONENTS	^{2]} $E_{TOT}(I_P) = \{[V_{IOUT_ideal}(I_P) - V_{IOUT}(I_P)] / [Sens_{ideal}(I_P) \times I_P]\} \times 100$	(%)			
Total Output Error ^[3]	_	$I_{P} = I_{PR(max)}, T_{A} = 25^{\circ}C \text{ to } 125^{\circ}C$	-1.5	±0.6	1.5	%
	E _{TOT}	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4	±1.5	4	%
Sensitivity Error	E _{SENS}	$I_P = I_{PR(max)}, T_A = 25^{\circ}C \text{ to } 125^{\circ}C$	-1.5	±0.5	1.5	%
Sensitivity End		$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4	±1.5	4	%
Offset Voltage	V _{OE}	I _P = 0 A, T _A = 25°C to 125°C	-10	±3.5	10	mV
		$I_P = 0 \text{ A}, T_A = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	-30	±9	30	mV
OVERCURRENT FAULT PER	FORMANCE					
		$VOC_F = 0.7 \times V_{CC}$, Positive I _P , T _A = 25°C	-10	±5	10	%
	E _{FF(HIGH)+}	$VOC_F = 0.7 \times V_{CC}$, Positive I _P , T _A = 25°C to 125°C	-10	±5	10	%
		$VOC_F = 0.7 \times V_{CC}$, Positive I _P , $T_A = -40$ °C to 25°C	_	±15	_	%
		$VOC_F = 0.7 \times V_{CC}$, Negative I _P , $T_A = 25^{\circ}C$	-10	±5	10	%
	E _{FF(HIGH)}	VOC_F = 0.7 × V _{CC} , Negative I _P , T _A = 25°C to 125°C	-10	±5	10	%
Fast Fault Error		VOC_F = $0.7 \times V_{CC}$, Negative I _P , T _A = -40° C to 25° C	_	±15	_	%
Tast Fault LITO		$VOC_F = 0.38 \times V_{CC}$, Positive I_P , $T_A = 25$ °C	-20	±15	20	%
	E _{FF(LOW)+}	$VOC_F = 0.38 \times V_{CC}$, Positive I _P , T _A = 25°C to 125°C	-20	±15	20	%
		$VOC_F = 0.38 \times V_{CC}$, Positive I_P , $T_A = -40^{\circ}C$ to 25°C	_	±25	-	%
		$VOC_F = 0.38 \times V_{CC}$, Negative I _P , $T_A = 25^{\circ}C$	-20	±15	20	%
	E _{FF(LOW)-}	VOC_F = 0.38 × V _{CC} , Negative I _P , T _A = 25°C to 125°C	-20	±15	20	%
		VOC_F = 0.38 × V_{CC} , Negative I_P , $T_A = -40$ °C to 25°C	_	±30	_	%
Slow Fault Error	E _{SF(HIGH)}	$VOC_S = 0.7 \times V_{CC}$, I_P rising	-6	±3	6	%
SIOW I AUIL LIIUI	E _{SF(LOW)}	VOC_S = 0.3 × V _{CC} , I _P rising	-10	±5	10	%

^[1] Typical values with +/- are 3 sigma values.



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^[2] A single part will not have both the maximum/minimum sensitivity error and maximum/minimum offset voltage, as that would violate the maximum/minimum total output error specification. Also, 3 sigma distribution values are combined by taking the square root of the sum of the squares. [3] Percentage of I_P , with $I_P = I_{PR(max)}$.

FAST AND SLOW FAULT SETTING AND FUNCTIONALITY

The ACS720 has two configurable overcurrent fault comparators which trip when the absolute value of the current through IP goes above the set threshold. There is a fast fault comparator, which reacts in approximately 1.5 μs to an overcurrent event, and there is a slow fault comparator which has a reacts in approximately 13 μs . The fast fault comparator operates on the Hall signal early in the signal chain, allowing for a fast response time but with limited accuracy. The slow fault comparator operates on a signal farther in the signal path, resulting a slower response time but with higher accuracy. The slow fault also adds additional digital filtering, which is why its response time is slower than that of the analog output.

The fault trip points are set using the VOC_F and VOC_S pins for the fast and slow fault trip points, respectively. The fault trip points are set using resistor dividers on the VOC_F and VOC_S pins. Setting the pin to $0.3 \times V_{CC}$ selects the minimum trip point, $I_{FAULT(F)(min)}$ or $I_{FAULT(S)(min)}$, and setting the pin to $0.7 \times V_{CC}$ selects the maximum trip point, $I_{FAULT(F)(max)}$ or $I_{FAULT(S)(max)}$. This can be seen in Figure 3. All voltages between $0.3 \times V_{CC}$ and $0.7 \times V_{CC}$ linearly select a trip point between the minimum and maximum levels, as shown in Figure 3. Refer to the performance characteristics tables for factory-tested fault trip points.

The resulting equation for the slow fault is:

$$I_{\text{FAULT(S)}} = \frac{V_{\text{OC(S)}} - 0.3 \times V_{\text{CC}}}{0.4 \times V_{\text{CC}}} \times (0.75 \times I_{\text{PR}}) + 0.5 \times I_{\text{PR}}$$
 (1)

This can be inverted to solve for the correct VOC_S level for a desired fault level:

$$V_{\text{OC(S)}} = \frac{(I_{\text{FAULT(S)}} - 0.5 \times I_{\text{PR}}) \times 0.4 \times V_{\text{CC}}}{0.75 \times I_{\text{PR}}} + (0.3 \times V_{\text{CC}})$$
 (2)

The resulting equation for the fast fault is:

$$I_{\text{FAULT(F)}} = \frac{V_{\text{OC(F)}} - 0.3 \times V_{\text{CC}}}{0.4 \times V_{\text{CC}}} \times (1.25 \times I_{\text{PR}}) + 1.0 \times I_{\text{PR}}$$
(3)

This can be inverted to solve for the correct VOC_F level for a desired fault level:

$$V_{\text{OC(F)}} = \frac{(I_{\text{FAULT(F)}} - 1.0 \times I_{\text{PR}}) \times 0.4 \times V_{\text{CC}}}{1.25 \times I_{\text{DP}}} + (0.3 \times V_{\text{CC}})$$
 (4)

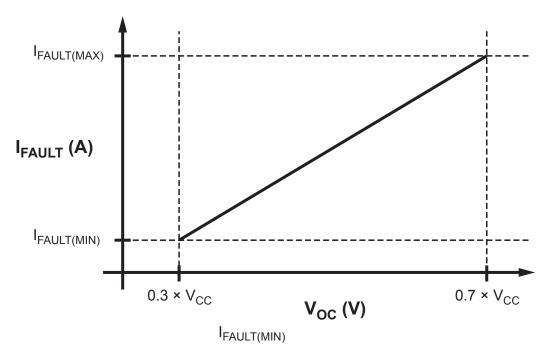


Figure 3: I_{FAULT} versus V_{OC}



In all cases, the VOC pins should be set to be a percentage of V_{CC} , which is easily done by using a resistor divider from V_{CC} to set the VOC pins (see Figure 4).

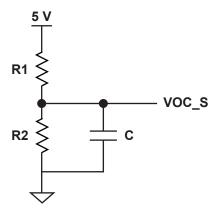


Figure 4: Resistor Divider

The ACS720 uses V_{CC} as a reference when reading the VOC pins, so even as V_{CC} changes, the fault trip level remains constant. The sample rate for the VOC pins is 62.5 kHz, so one should filter the voltage on the VOC pins to below 31 kHz to avoid aliasing. This is simply done by adding a capacitor to ground on the VOC pins (see Figure 4). The filter bandwidth will be:

$$f = \frac{1}{2\pi \times (R1||R2) \times C} = \frac{1}{2\pi \times \left(\frac{R1 \times R2}{R1 + R2}\right) \times C}$$
 (5)

The VOC update rate is 7.8 kHz allowing for eight samples to be averaged per update.

FAULT DELAY AND HYSTERESIS

When the absolute current flowing through IP goes above I_{FAULT} for either the fast or slow fault, the respective comparator will trip (1), and $t_{R(SF/FF)}$ later, the respective fault pin will go low (2). When the current decreases to $I_{FAULT} - I_{HYS}$, the fault pin will go high (3). If the current goes above I_{FAULT} but then decreases

below $I_{FAULT} - I_{HYS}$ before $t_{R(SF/FF)}$, the fault pin will stay high (4). However, if the current goes above I_{FAULT} and then decreases below I_{FAULT} but above $I_{FAULT} - I_{HYS}$, the fault pin will go low $t_{R(SF/FF)}$ after the current went above I_{FAULT} (5).

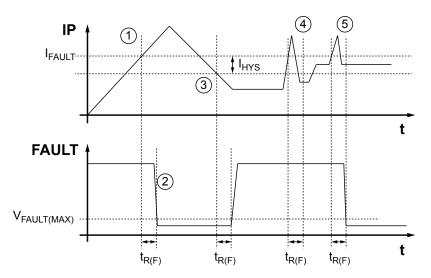


Figure 5: Fault Delay and Hysteresis



DEFINITIONS OF ACCURACY CHARACTERISTICS

Sensitivity (Sens). The change in sensor IC output in response to a 1A change through the primary conductor. The sensitivity is the product of the magnetic circuit sensitivity (G/A) (1 G = 0.1 mT) and the linear IC amplifier gain (mV/G). The linear IC amplifier gain is programmed at the factory to optimize the sensitivity (mV/A) for the full-scale current of the device.

Nonlinearity (E_{LIN}). The nonlinearity is a measure of how linear the output of the sensor IC is over the full current measurement range. The nonlinearity is calculated as:

$$E_{\text{LIN}} = \left\{ 1 - \left[\frac{V_{\text{IOUT}}(I_{\text{PR(max)}}) - V_{\text{IOUT(Q)}}}{2 \times V_{\text{IOUT}}(I_{\text{PR(max)}}/2) - V_{\text{IOUT(Q)}}} \right] \right\} \times 100(\%)$$
 (6)

where $V_{IOUT}(I_{PR(max)})$ is the output of the sensor IC with the maximum measurement current flowing through it and $V_{IOUT}(I_{PR(max)}/2)$ is the output of the sensor IC with half of the maximum measurement current flowing through it.

Zero-Current Output Voltage (V_{IOUT(Q)}). The output of the sensor when the primary current is zero. $V_{IOUT(Q)}$ is nominally 1.5 V. Variation in $V_{IOUT(Q)}$ can be attributed to the resolution of the Allegro linear IC quiescent voltage trim and thermal drift.

Offset Voltage (V_{OE}). The deviation of the device output from its ideal quiescent value of 1.5 V due to nonmagnetic causes. To convert this voltage to amperes, divide by the device sensitivity, Sens.

Total Output Error (E_{TOT}). The difference between the current measurement from the sensor IC and the actual current (I_p), relative to the actual current. This is equivalent to the difference between the ideal output voltage and the actual output voltage, divided by the ideal sensitivity, relative to the current flowing through the primary conduction path:

$$E_{\text{TOT}}(I_{\text{P}}) = \frac{V_{\text{IOUT_ideal}}(I_{\text{P}}) - V_{\text{IOUT}}(I_{\text{P}})}{Sens_{\text{ideal}}(I_{\text{P}}) \times I_{\text{P}}} \times 100 \,(\%) \tag{7}$$

The Total Output Error incorporates all sources of error and is a function of I_P . At relatively high currents, E_{TOT} will be mostly due to sensitivity error, and at relatively low currents, E_{TOT} will be mostly due to Offset Voltage (V_{OE}). In fact, at $I_P=0$, E_{TOT} approaches infinity due to the offset. This is illustrated in Figure 6 and Figure 7. Figure 6 shows a distribution of output voltages versus I_P at 25°C and across temperature. Figure 7 shows the corresponding E_{TOT} versus I_P .

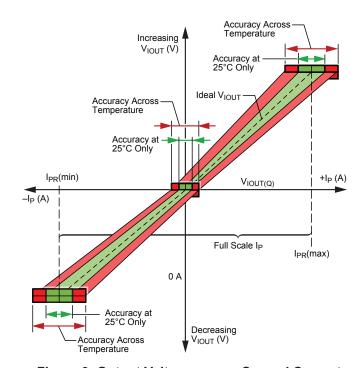


Figure 6: Output Voltage versus Sensed Current

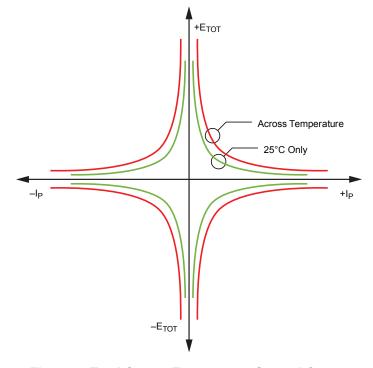


Figure 7: Total Output Error versus Sensed Current



Common Mode Field Rejection

Common Mode Field Rejection (CMFR) measures the ability of the device to reject common-mode magnetic signals. It is defined as the ratio between the voltage swing due to a magnetic field divided by the magnetic field and the gain of the sensor in dB.

$$CMFR = 20 \log_{10} \left| \frac{A_{CM}}{Sens/CF} \right|$$

where A_{CM} is the gain measured due to an external field in mV/G and CF is the coupling factor of the integrated current loop.

For a sensitivity (Sens) of 50 mV/A, a coupling factor or 12 G/A, a CMFR of –40 dB and a 1 G external field, the output will swing 6 mV.

Power Supply Rejection Ratio

Sensitivity Power Supply Rejection Ratio (PSRRS).

The ratio of the percent change in sensitivity from the sensitivity at nominal supply voltage (V_{CCN}) to the percent change in V_{CC} in dB.

$$PSRR_{S} = 20 \log_{10} \left| \frac{[Sens_{Vccn} \times (V_{CC} - V_{CCN})]}{[(Sens_{Vcc} - Sens_{Vccn}) \times V_{CCN}]} \right|$$

A PSRR $_{\rm S}$ value of 40 dB means that a 5% change in V $_{\rm CC}$ (going from 5 to 5.25 V, for example) results in around a 0.05% change in sensitivity.

Quiescent Voltage Power Supply Rejection Ratio (PSRRQ).

The ratio of the change in quiescent voltage to the change in V_{CC} in dB.

$$PSRR_Q = 20 \log_{10} \left| \frac{(\Delta V_{CC})}{(\Delta V_{IOUT(Q)})} \right|$$

A PSRR $_{\rm Q}$ value of 40 dB means a 250 mV change in V $_{\rm CC}$ (going from 5 to 5.25 V, for example) results in a 2.5 mV change in quiescent voltage.



DEFINITIONS OF DYNAMIC RESPONSE CHARACTERISTICS

Power-On Time (t_{PO}) . When the supply is ramped to its operating voltage, the device requires a finite time to power its internal components before responding to an input magnetic field. Power-On Time, t_{PO} , is defined as the time it takes for the output voltage to settle within $\pm 10\%$ of its steady-state value under an applied magnetic field, after the power supply has reached its minimum specified operating voltage, V_{CC}(min), as shown in the chart at right.

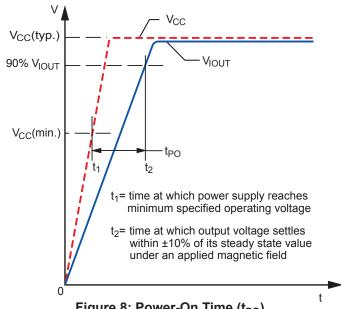


Figure 8: Power-On Time (t_{PO})

Rise Time (t_r) . The time interval between a) when the sensor IC reaches 10% of its full-scale value, and b) when it reaches 90% of its full-scale value. The rise time to a step response is used to derive the bandwidth of the current sensor IC, in which f(-3 dB)= $0.35/t_r$. Both t_r and $t_{RESPONSE}$ are detrimentally affected by eddy-current losses observed in the conductive IC ground plane.

Propagation Delay (t_{pd}) . The propagation delay is measured as the time interval a) when the primary current signal reaches 20% of its final value, and b) when the device reaches 20% of its output corresponding to the applied current.

Response Time ($t_{RESPONSE}$). The time interval between a) when the primary current signal reaches 90% of its final value, and b) when the device reaches 90% of its output corresponding to the applied current.

Fault Response Time (t_{RFF} , t_{RSF}). The time interval between a) when the primary current signal reaches the fault threshold, and b) when the device fault pin reacts to the current event. A current of 20% above the fault trip level should be used to guarantee fault timing.

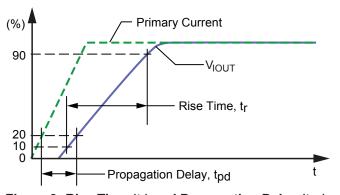


Figure 9: Rise Time (t_r) and Propagation Delay (t_{nd})

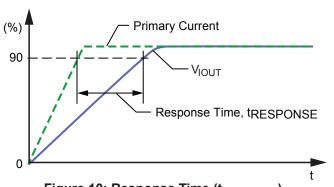
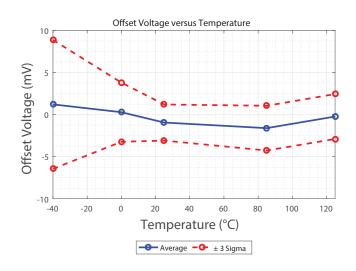
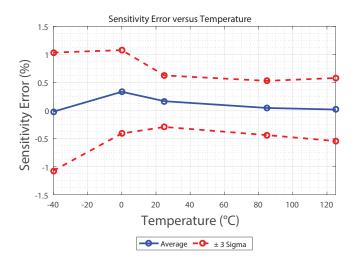


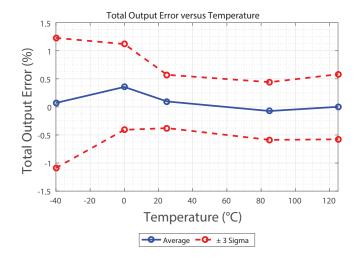
Figure 10: Response Time (t_{RESPONSE})



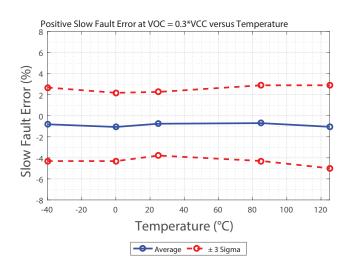
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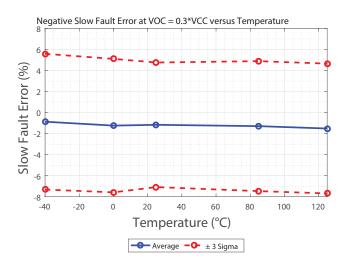


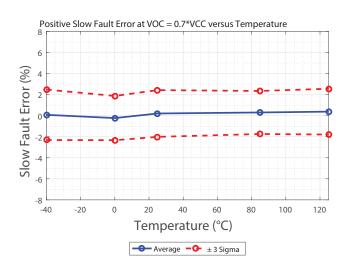


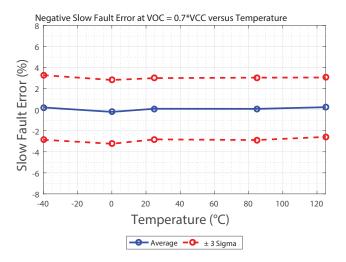


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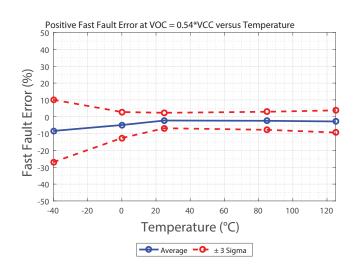


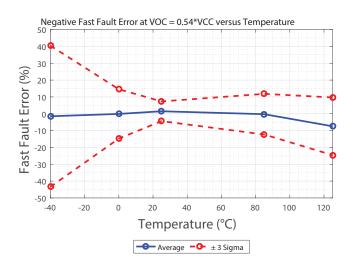


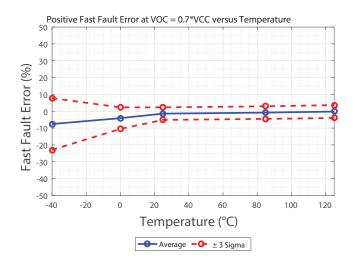


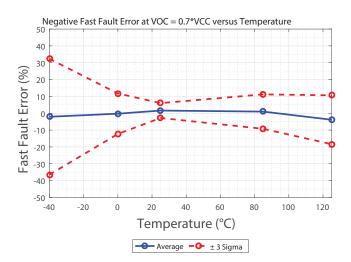


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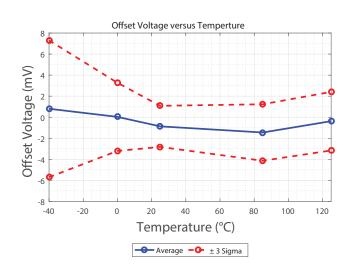


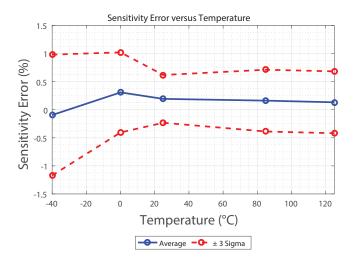


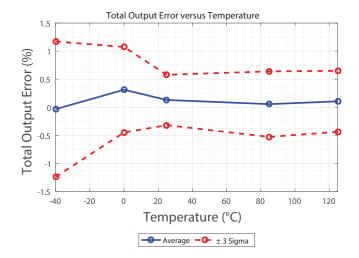




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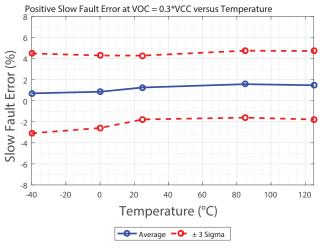


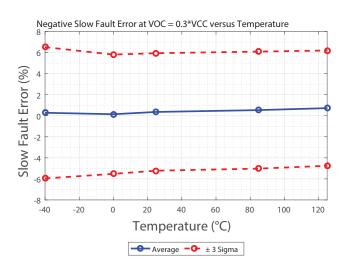


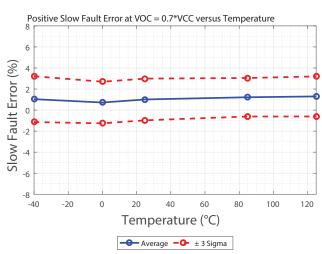


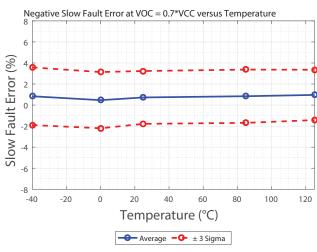


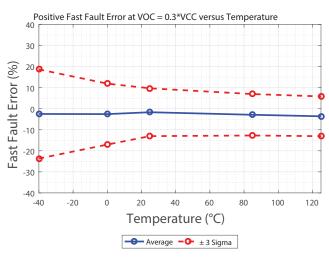
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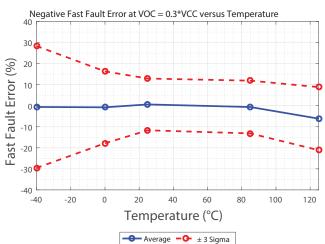




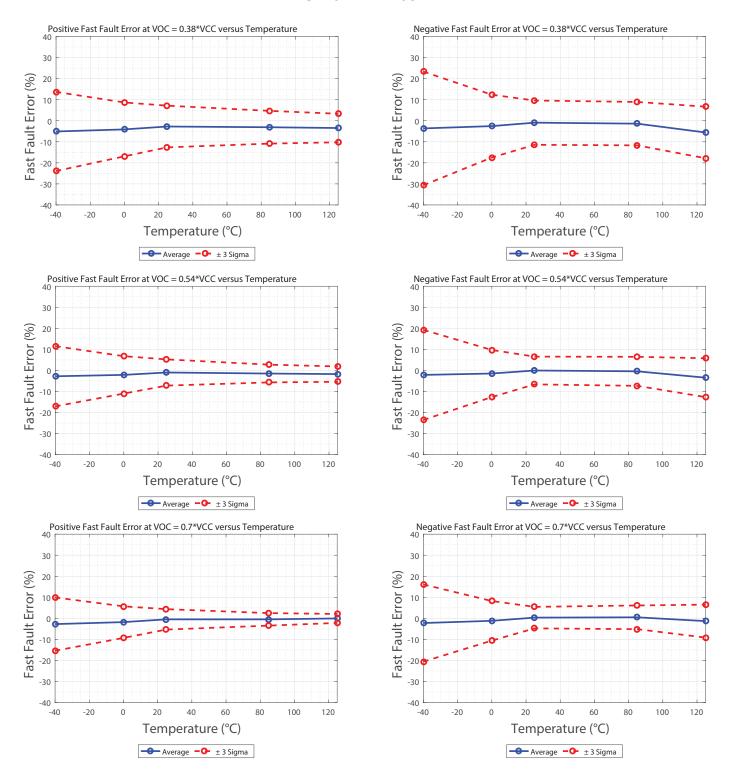




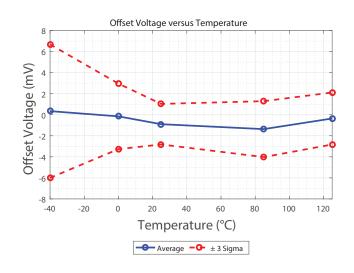


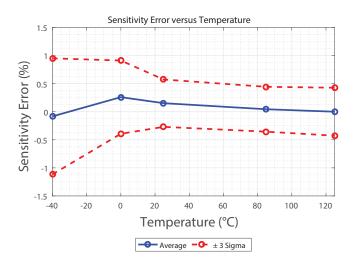


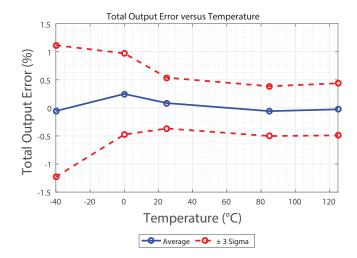
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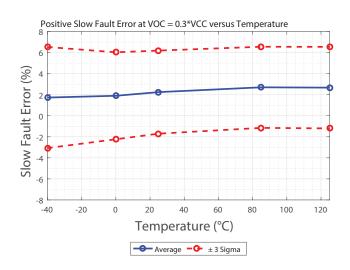


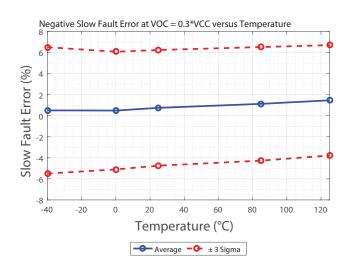


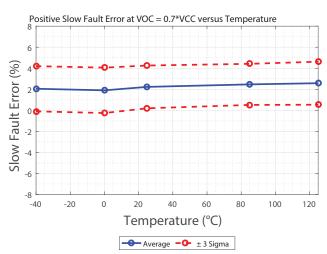


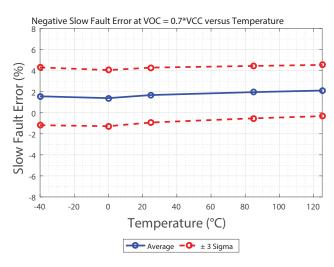


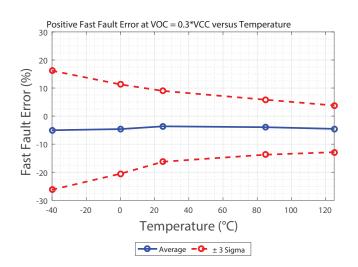
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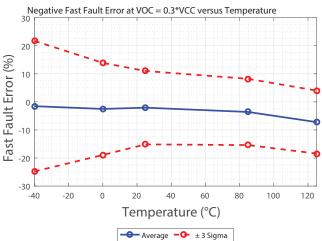




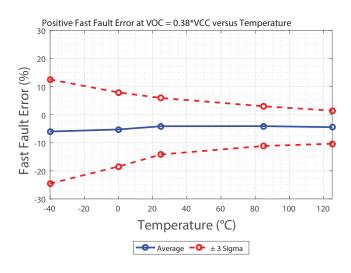


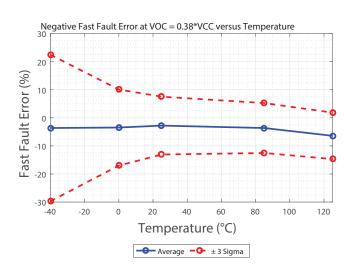


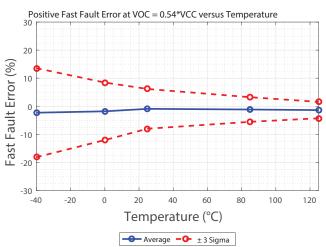


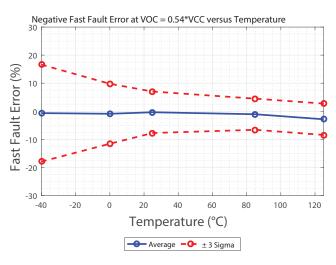


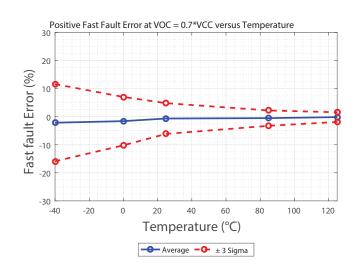
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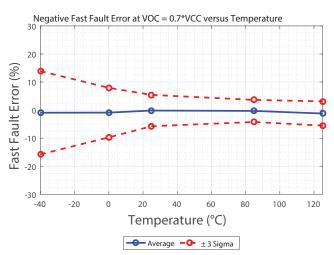






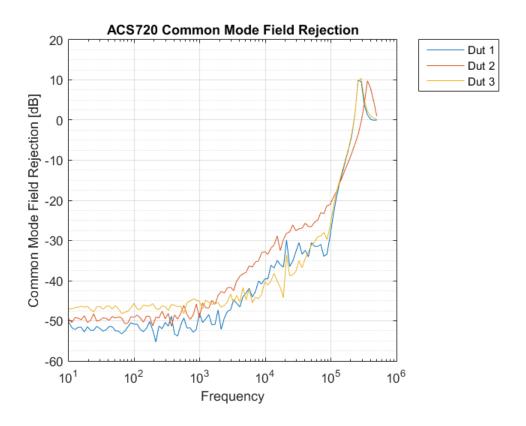




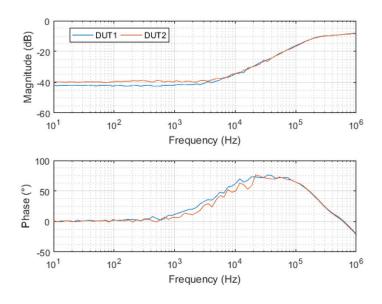




CHARACTERIZATION DATA



Power Supply Rejection Ratio





RECOMMENDED PCB LAYOUT

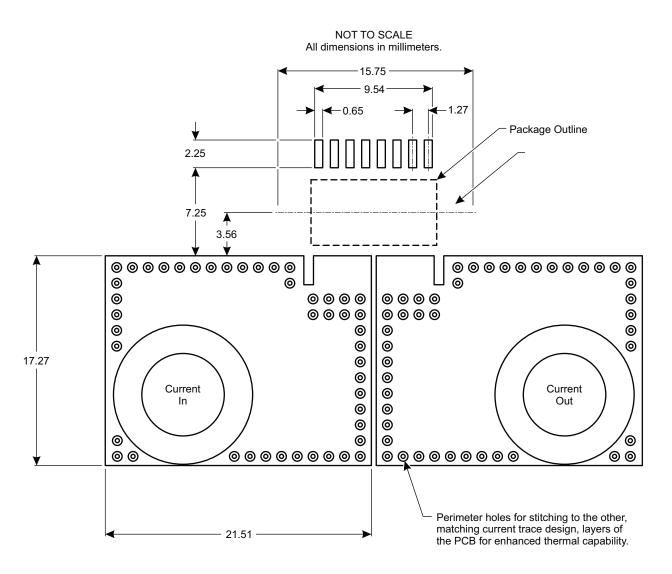


Figure 11: High Isolation PCB Layout

For additional information on layout, see:

http://www.allegromicro.com/en/Design-Center/Technical-Documents/Hall-Effect-Sensor-IC-Publications/Techniques-Minimize-Common-Mode-Field-Interference.aspx



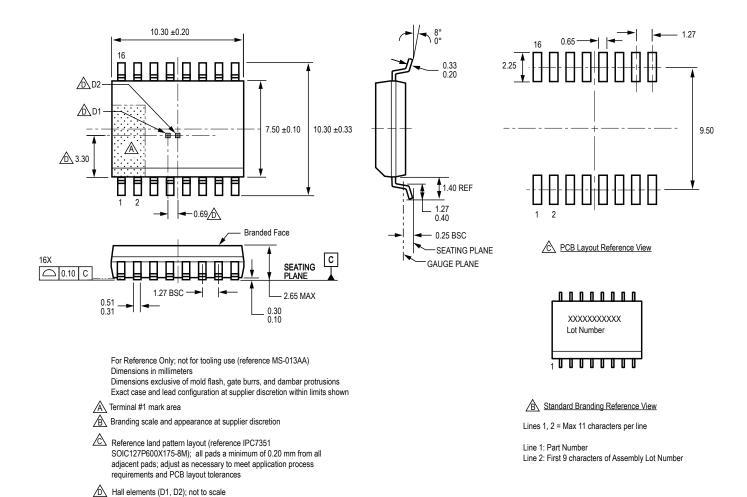


Figure 12: Package LA, 16-pin SOICW

High Accuracy, Dual Fault, Galvanically Isolated Current Sensor in SOIC16 Widebody Package

Revision History

Number	Date	Description
_	August 30, 2017	Initial release
1	November 13, 2017	Corrected typo in Dielectric Surge Strength Test Voltage notes of Isolation Characteristics table (p. 3)
2	December 12, 2017	Corrected branding information (p. 25)

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